



N-Channel 100-V (D-S), 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
100	0.0185 at V _{GS} = 10 V	50	48 nC

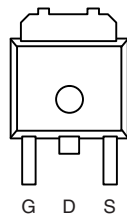
FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested



APPLICATIONS

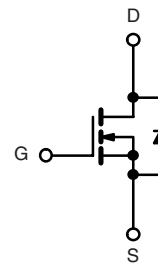
- Primary Side Switch
- Isolated DC/DC Converter



Top View

Drain Connected to Tab

Ordering Information: SUD50N10-18P-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	50 ^a	A
		T _C = 100 °C	39	
		T _A = 25 °C	8.2 ^b	
		T _A = 100 °C	5.8 ^b	
Pulsed Drain Current	I _{DM}	100		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	50 ^a	
		T _A = 25 °C	2.0 ^b	
Single Pulse Avalanche Current	I _{AS}	45		
Avalanche Energy	E _{AS}	101	mJ	
Maximum Power Dissipation	P _D	T _C = 25 °C	136.4	W
		T _C = 100 °C	68.2	
		T _A = 25 °C	3.0 ^b	
		T _A = 100 °C	1.5 ^b	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^b	R _{thJA}	40	50	°C/W	
Maximum Junction-to-Case	R _{thJC}	0.85	1.1		

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		110		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 12.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.015	0.0185	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		33		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2600		pF
Output Capacitance	C_{oss}			230		
Reverse Transfer Capacitance	C_{rss}			80		
Total Gate Charge	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		48	75	nC
Gate-Source Charge	Q_{gs}			16		
Gate-Drain Charge	Q_{gd}			13		
Gate Resistance	R_g		$f = 1\text{ MHz}$		1.6	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 1.0\text{ }\Omega$ $I_D \cong 50\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		12	20	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			18	35	
Fall Time	t_f			8	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			50	A
Pulse Diode Forward Current ^a	I_{SM}				100	
Body Diode Voltage	V_{SD}	$I_S = 15\text{ A}$		0.85	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		80	120	ns
Body Diode Reverse Recovery Charge	Q_{rr}			160	240	nC
Reverse Recovery Fall Time	t_a			57		ns
Reverse Recovery Rise Time	t_b			23		

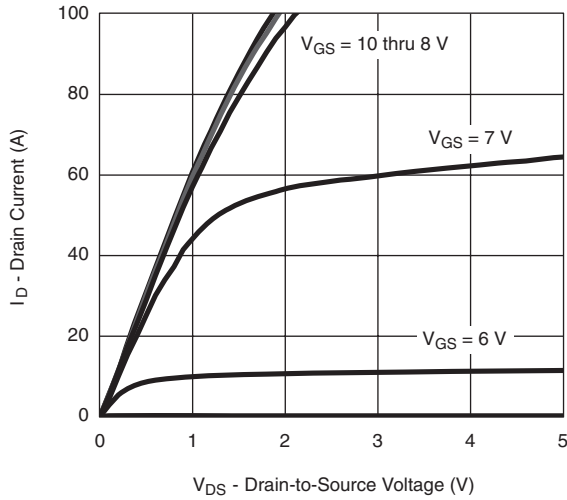
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

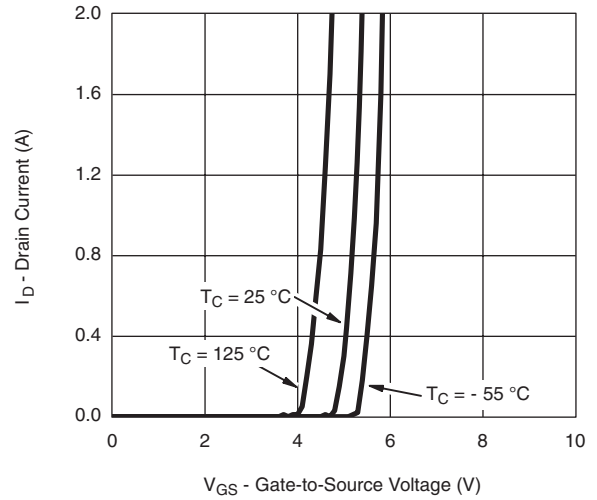
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



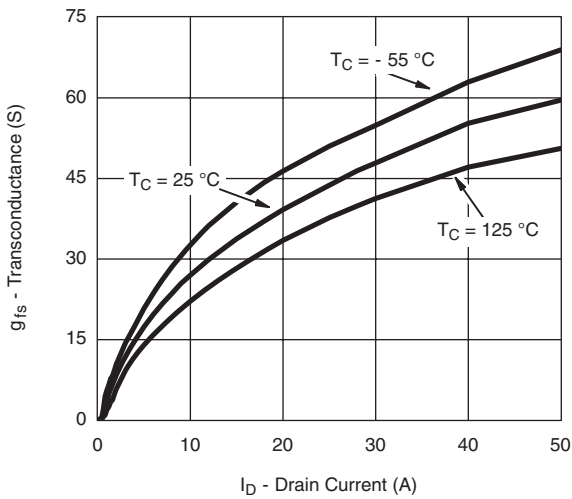
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



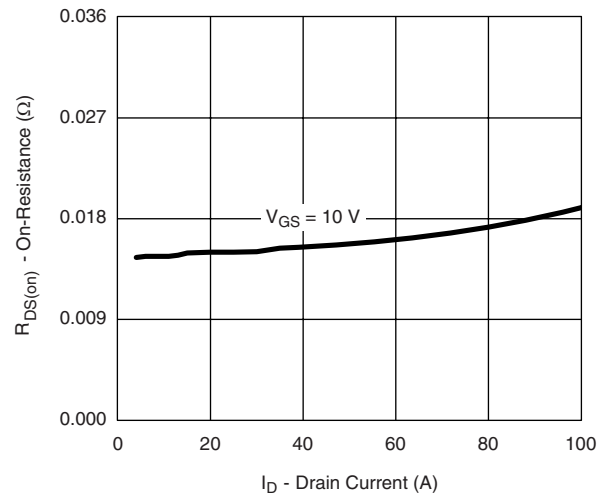
Output Characteristics



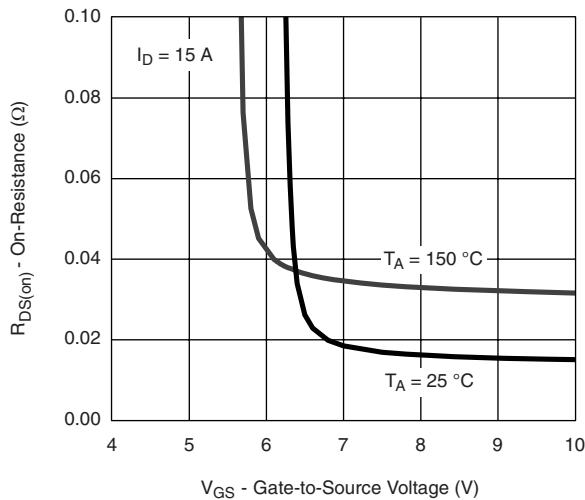
Transfer Characteristics



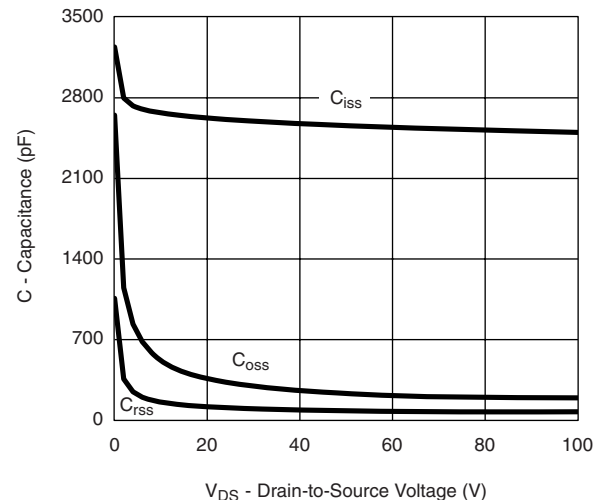
Transconductance



On-Resistance vs. Drain Current



On-Resistance vs. Gate-to-Source Voltage



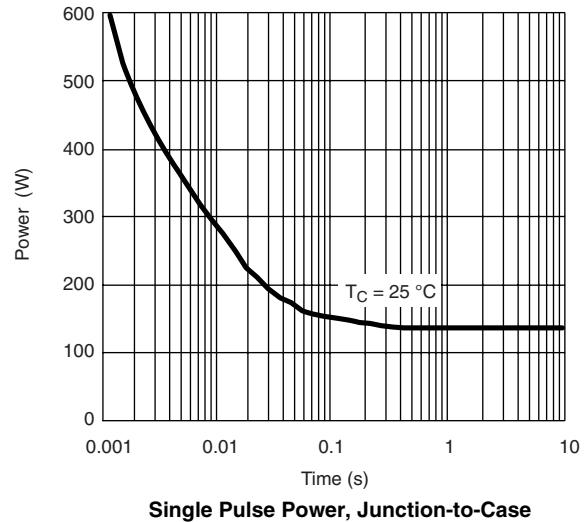
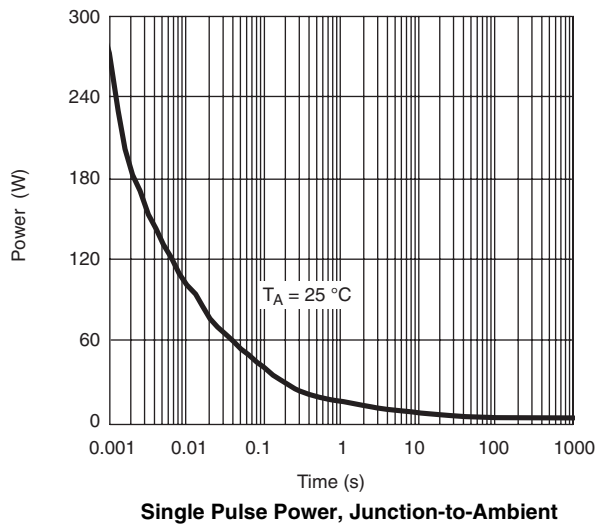
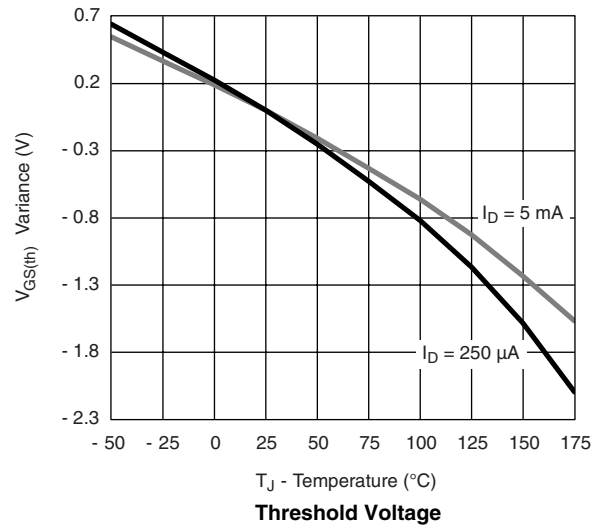
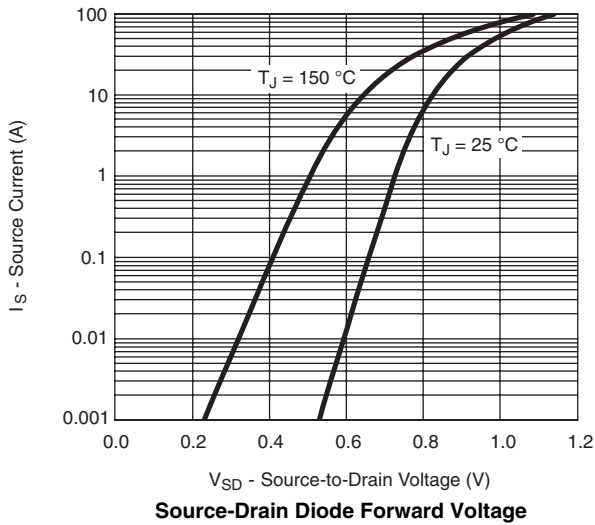
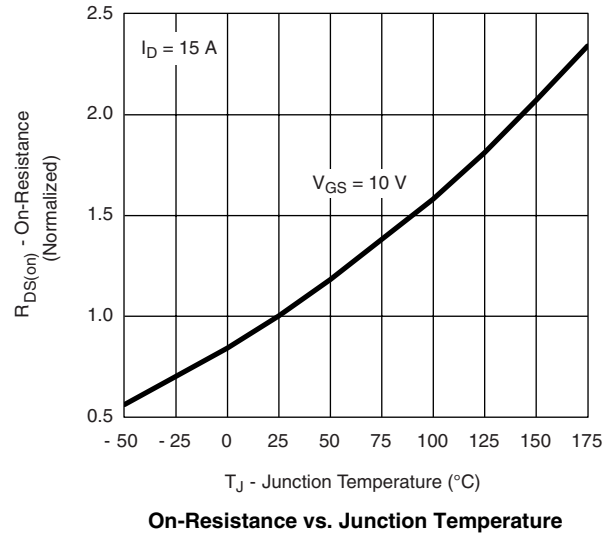
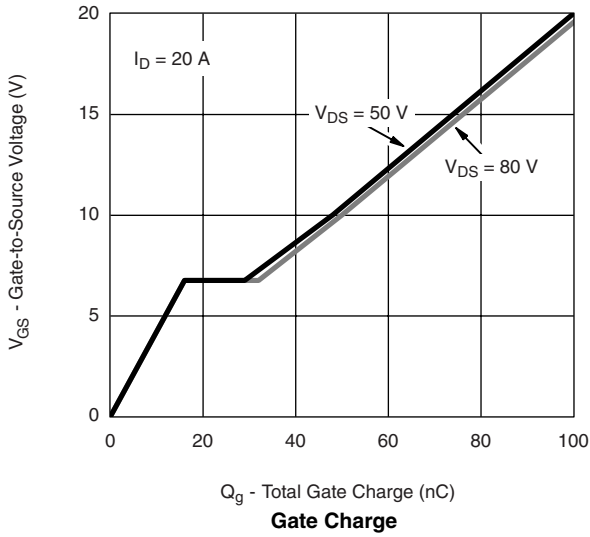
Capacitance

SUD50N10-18P



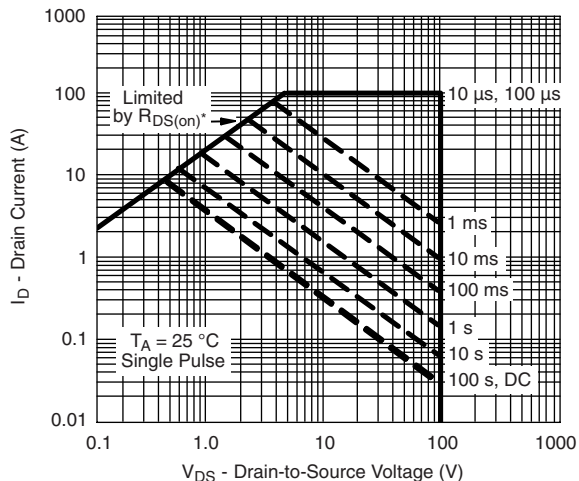
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

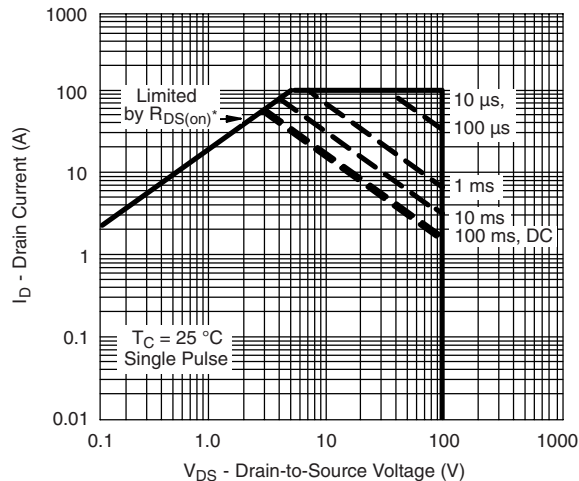




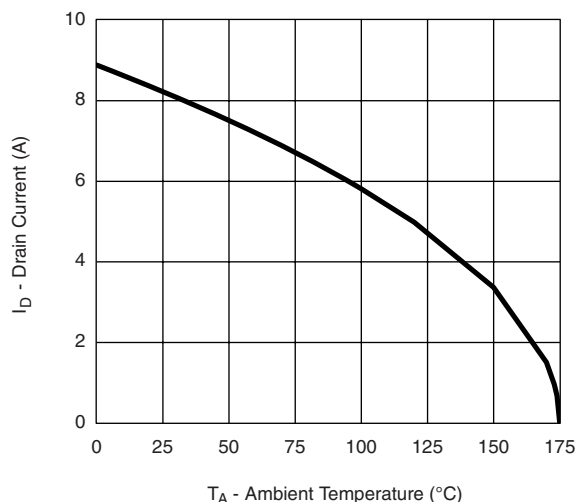
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



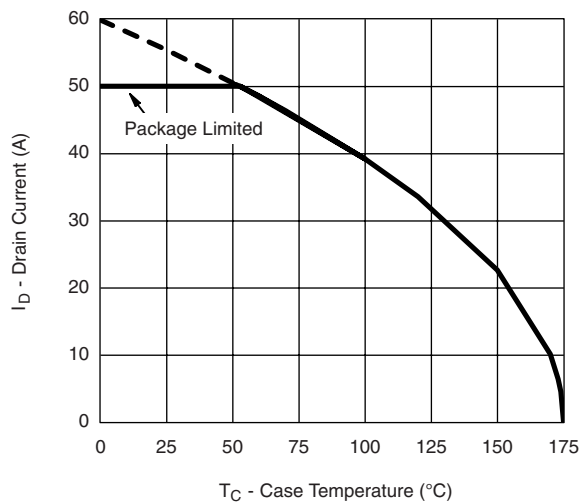
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Case



Current Derating, Junction-to-Ambient**



Current Derating, Junction-to-Case**

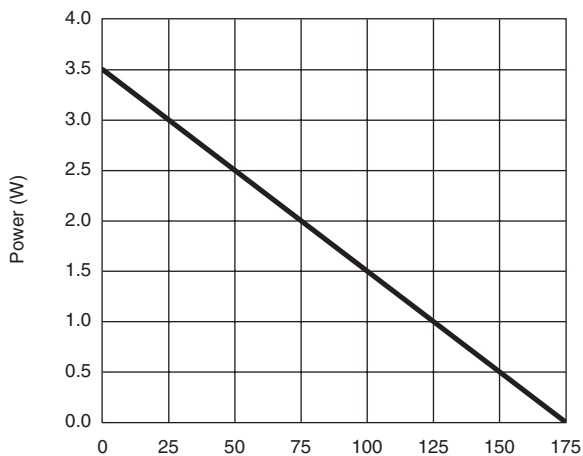
** The power dissipation P_D is based on $T_{J(max)} = 175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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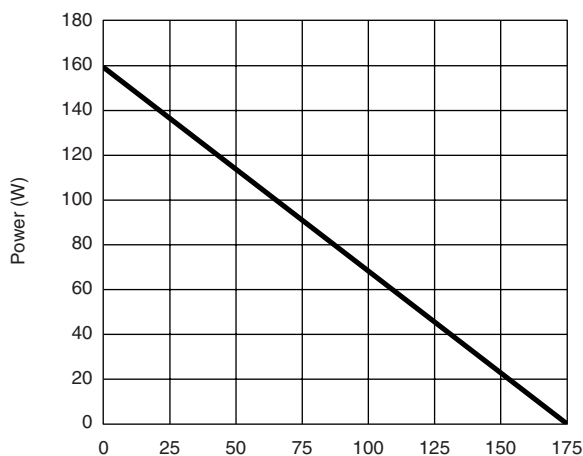


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TA - Ambient Temperature (°C)
Power Derating , Junction-to-Ambient**

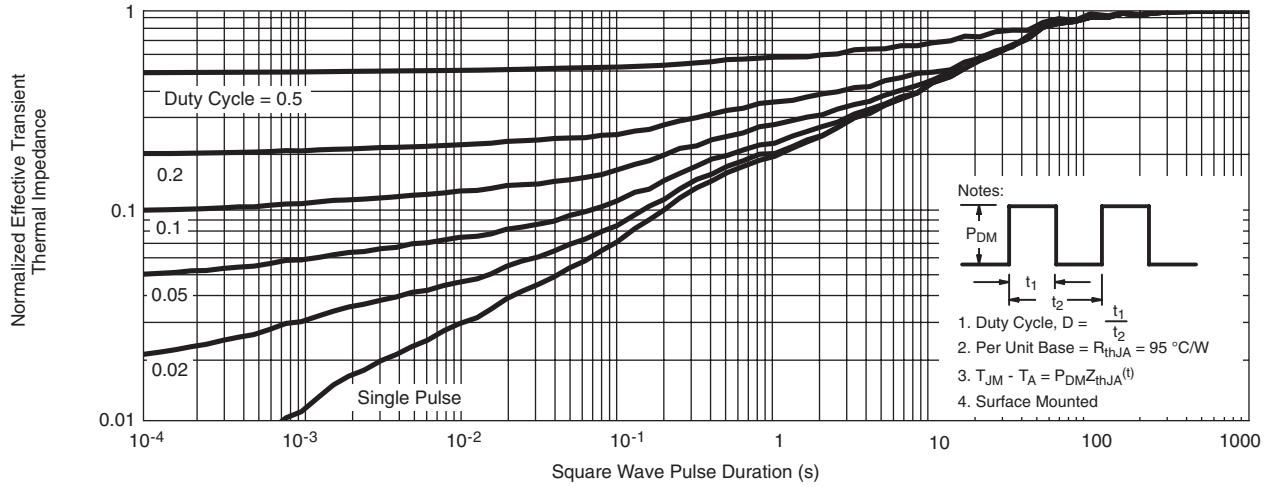


TC - Case Temperature (°C)
Power Derating , Junction-to-Case**

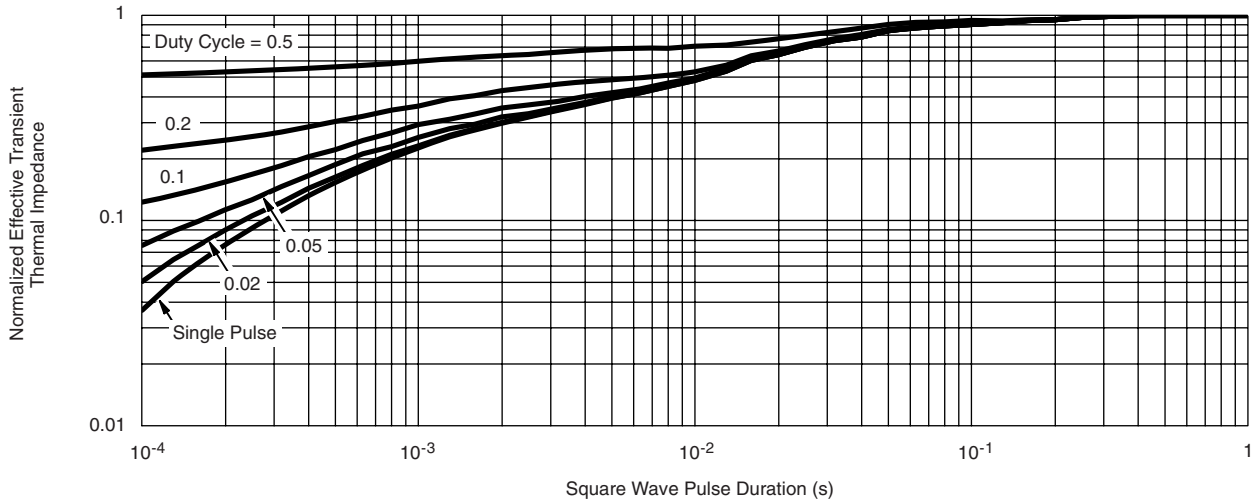
** The power dissipation P_D is based on $T_{J(max)} = 175\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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